

N-channel TrenchMOS standard level FET

Rev. 3 — 13 October 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using Nexperia High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Q101 compliant
- Suitable for standard level gate drive sources

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- DC-to-DC converters
- Engine management

1.4 Quick reference data

Table 1. Quick reference data

resistance

Symbol Parameter Conditions Min Unit Тур Max T_i ≥ 25 °C; T_i ≤ 175 °C ٧ V_{DS} drain-source 100 voltage I_D drain current $V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ 24.8 A see Figure 1; see Figure 4 P_{tot} total power T_{mb} = 25 °C; see Figure 2 85 W dissipation **Static characteristics** drain-source $V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ 40 53 mΩ R_{DSon} $T_i = 25 \text{ °C}; \text{ see } Figure 12;$ on-state

see Figure 13

- Suitable for thermally demanding environments due to 175 °C rating
- General purpose power switching
- Solenoid drivers
- Transmission control



N-channel TrenchMOS standard level FET

Table 1. Quick reference datacontinued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 24.8 \text{ A}; \ V_{sup} \leq 100 \text{ V}; \\ R_{GS} &= 50 \ \Omega; \ V_{GS} = 10 \text{ V}; \\ T_{j(init)} &= 25 \ ^\circ\text{C}; \ unclamped \end{split} $	-	-	81	mJ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	I_D = 10 A; V_{DS} = 80 V; V_{GS} = 10 V; see <u>Figure 14</u>	-	8.5	-	nC

2. Pinning information

Table 2.Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	С	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$\begin{array}{c} \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \end{array} \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \end{array} \begin{array}{c} \\ \\ \\ \\ \\ \\ \\ \\ \end{array} \end{array}$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3.	Ordering in	formation		
Type number F		Package		
		Name	Description	Version
BUK7Y53-1	00B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

N-channel TrenchMOS standard level FET

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

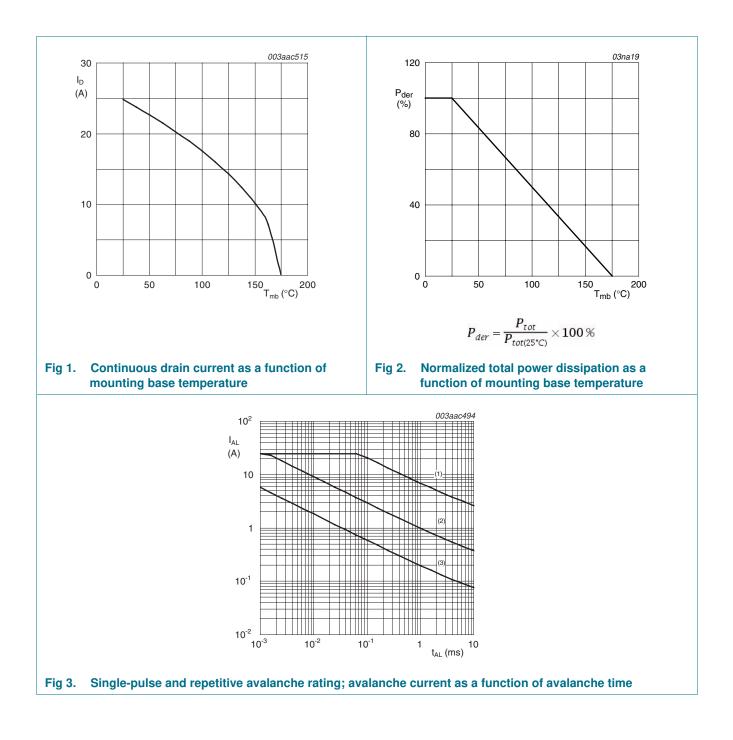
Parameter	Conditions		Min	Max	Unit
drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	100	V
gate-source voltage			-20	20	V
drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>		-	24.8	А
	T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>		-	17.6	А
peak drain current	$T_{mb} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed};$ see Figure 4		-	99	А
total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	85	W
storage temperature			-55	175	°C
junction temperature			-55	175	°C
diode					
source current	T _{mb} = 25 °C		-	24.8	А
peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C		-	99	А
ggedness					
non-repetitive drain-source avalanche energy	I_D = 24.8 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	81	mJ
repetitive drain-source avalanche energy	see Figure 3	[1][2][3]	-	-	J
	drain-source voltage drain-gate voltage gate-source voltage drain current peak drain current total power dissipation storage temperature junction temperature diode source current peak source current ggedness non-repetitive drain-source avalanche energy repetitive drain-source	$\begin{array}{ccc} drain-source voltage & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} \\ drain-gate voltage & R_{GS} = 20 \ \text{k}\Omega \\ gate-source voltage & & & \\ drain current & T_{mb} = 25 \ ^{\circ}\text{C}; \ V_{GS} = 10 \ \text{V}; \ \text{see Figure 1}; \\ \text{see Figure 4} \\ T_{mb} = 100 \ ^{\circ}\text{C}; \ V_{GS} = 10 \ \text{V}; \ \text{see Figure 1} \\ \text{peak drain current} & T_{mb} = 25 \ ^{\circ}\text{C}; \ t_{p} \leq 10 \ \text{\mus}; \ \text{pulsed}; \\ \text{see Figure 4} \\ \text{total power dissipation} & T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see Figure 2} \\ \text{storage temperature} \\ \text{junction temperature} \\ \hline \textbf{diode} \\ \text{source current} & T_{mb} = 25 \ ^{\circ}\text{C} \\ \text{peak source current} & t_{p} \leq 10 \ \text{\mus}; \ \text{pulsed}; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ \text{gedness} \\ \hline \text{non-repetitive drain-source} & I_{D} = 24.8 \ \text{A}; \ V_{sup} \leq 100 \ \text{V}; \ \text{R}_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ \text{unclamped} \\ \text{repetitive drain-source} & \text{see Figure 3} \\ \end{array}$	$\begin{array}{ccc} drain-source voltage & T_{j} \geq 25 \ ^{\circ}\text{C}; \ T_{j} \leq 175 \ ^{\circ}\text{C} \\ \\ drain-gate voltage & R_{GS} = 20 \ \text{k}\Omega \\ \\ gate-source voltage \\ \\ drain current & T_{mb} = 25 \ ^{\circ}\text{C}; \ V_{GS} = 10 \ \text{V}; \ \text{see } \underline{Figure 1}; \\ & \underline{see \ Figure 4} \\ \hline T_{mb} = 100 \ ^{\circ}\text{C}; \ V_{GS} = 10 \ \text{V}; \ \text{see } \underline{Figure 1} \\ \\ peak \ drain \ current & T_{mb} = 25 \ ^{\circ}\text{C}; \ t_{p} \leq 10 \ \mu\text{s}; \ \text{pulsed}; \\ & \underline{see \ Figure 4} \\ \hline total \ power \ dissipation & T_{mb} = 25 \ ^{\circ}\text{C}; \ \text{see } \underline{Figure 2} \\ & \underline{storage \ temperature} \\ \hline junction \ temperature \\ \hline \textbf{diode} \\ & \underline{source \ current} & T_{mb} = 25 \ ^{\circ}\text{C} \\ & \underline{peak \ source \ current} & T_{mb} = 25 \ ^{\circ}\text{C} \\ & \underline{peak \ source \ current} & t_{p} \leq 10 \ \mu\text{s}; \ \text{pulsed}; \ T_{mb} = 25 \ ^{\circ}\text{C} \\ \hline \textbf{gedness} \\ & \underline{non-repetitive \ drain-source} & I_{D} = 24.8 \ \text{A}; \ V_{sup} \leq 100 \ \text{V}; \ R_{GS} = 50 \ \Omega; \\ & V_{GS} = 10 \ \text{V}; \ T_{j(init)} = 25 \ ^{\circ}\text{C}; \ unclamped \\ \hline \textbf{repetitive \ drain-source} & see \ \underline{Figure 3} \\ \hline \begin{array}{c} 111213 \\ \hline 111213 \end{array}$	$\begin{array}{cccc} drain-source \mbox{ voltage } & T_j \geq 25\ {}^\circ\mbox{C};\ T_j \leq 175\ {}^\circ\mbox{C} & - & & & & & & & & & & & & & & & & & $	$\begin{array}{cccc} drain-source voltage & T_j \geq 25\ ^{\circ} C;\ T_j \leq 175\ ^{\circ} C & - & 100 \\ \\ drain-gate voltage & R_{GS} = 20\ k\Omega & - & 100 \\ \\ gate-source voltage & -20 & 20 \\ \\ drain current & T_{mb} = 25\ ^{\circ} C;\ V_{GS} = 10\ V;\ see\ Figure\ 1; & - & 24.8 \\ \\ see\ Figure\ 4 & T_{mb} = 100\ ^{\circ} C;\ V_{GS} = 10\ V;\ see\ Figure\ 1 & - & 17.6 \\ \\ peak\ drain\ current & T_{mb} = 25\ ^{\circ} C;\ t_p \leq 10\ \mu s;\ pulsed; & - & 99 \\ see\ Figure\ 4 & - & -55 & 175 \\ \\ junction\ temperature & -55 & 175 \\ \\ junction\ temperature & T_{mb} = 25\ ^{\circ} C;\ see\ Figure\ 2 & - & 85 \\ \\ source\ current & T_{mb} = 25\ ^{\circ} C \\ source\ current & T_{mb} = 25\ ^{\circ} C \\ \\ peak\ source\ current & T_{mb} = 25\ ^{\circ} C \\ \\ \\ peak\ source\ current & T_{mb} = 25\ ^{\circ} C \\ \\ \\ \\ peak\ source\ current & t_p \leq 10\ \mu s;\ pulsed;\ T_{mb} = 25\ ^{\circ} C \\ \\ \\ \\ \\ rob = 24.8\ A;\ V_{sup} \leq 100\ V;\ R_{GS} = 50\ \Omega; \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ $

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[2] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

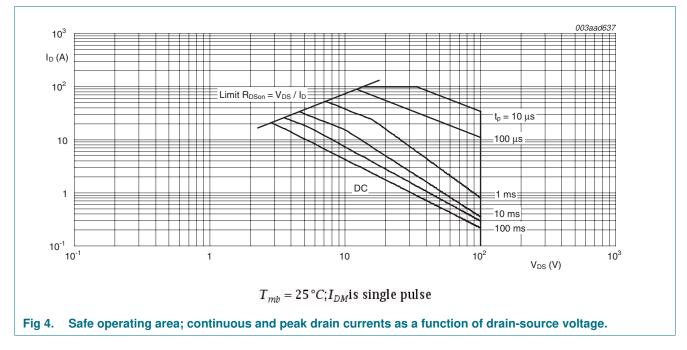
[3] Refer to application note AN10273 for further information.

BUK7Y53-100B



BUK7Y53-100B

N-channel TrenchMOS standard level FET



5. Thermal characteristics

Table 5.Thermal characteristics

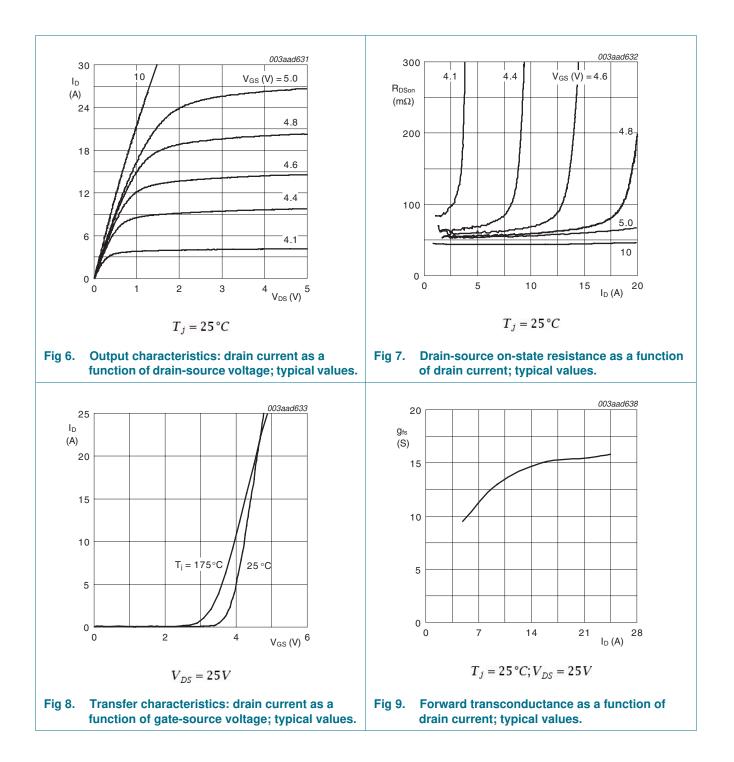


N-channel TrenchMOS standard level FET

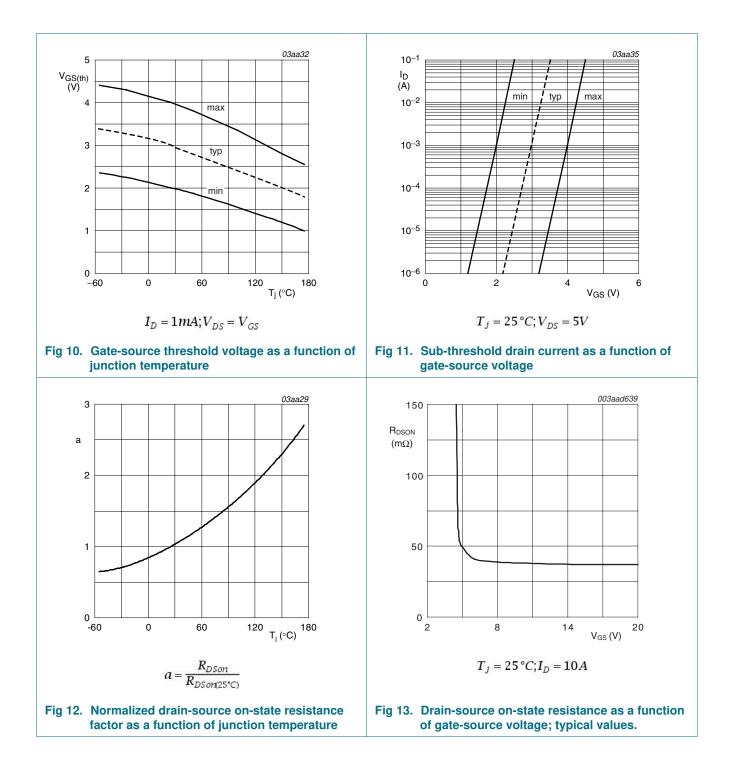
6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V _{(BR)DSS} drain-source		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
()	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
DSS	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{DS} = 0 V; V _{GS} = 20 V; T _j = 25 °C	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
Boom	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12; see Figure 13	-	-	138	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	40	53	mΩ
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u>	-	22	-	nC
Q _{GS}	gate-source charge		-	4.3	-	nC
Q _{GD}	gate-drain charge		-	8.5	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1100	1467	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{15}$	-	142	170	pF
C _{rss}	reverse transfer capacitance		-	63	86	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 3 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	15.3	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	7.8	-	ns
d(off)	turn-off delay time		-	34	-	ns
f	fall time		-	7.7	-	ns
Source-drai	in diode					
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 25 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 16</u>	-	0.85	1.2	V
rr	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	56	-	ns
Q _r	recovered charge	$V_{DS} = 30 V$	-	155	-	nC

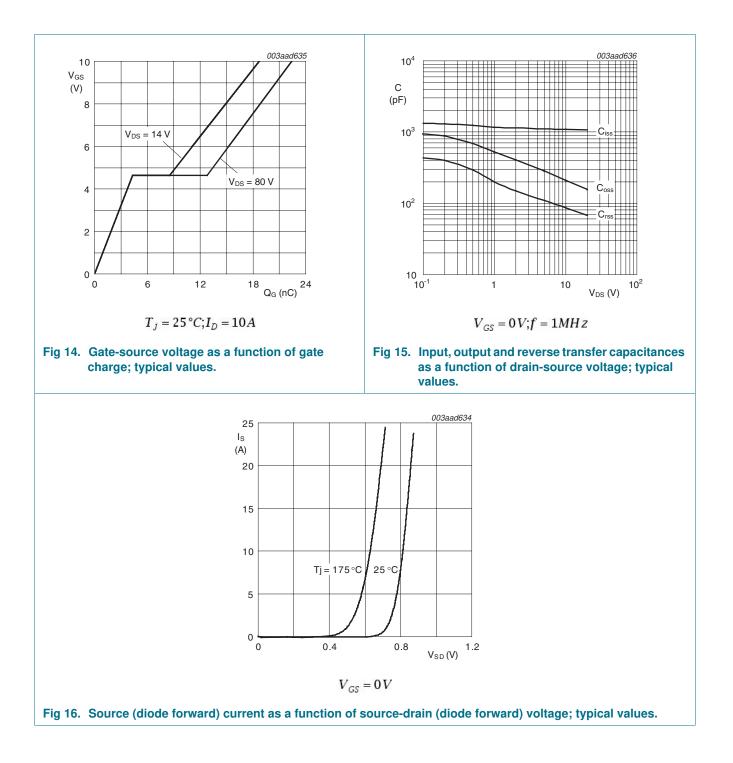
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N-channel TrenchMOS standard level FET

7. Package outline

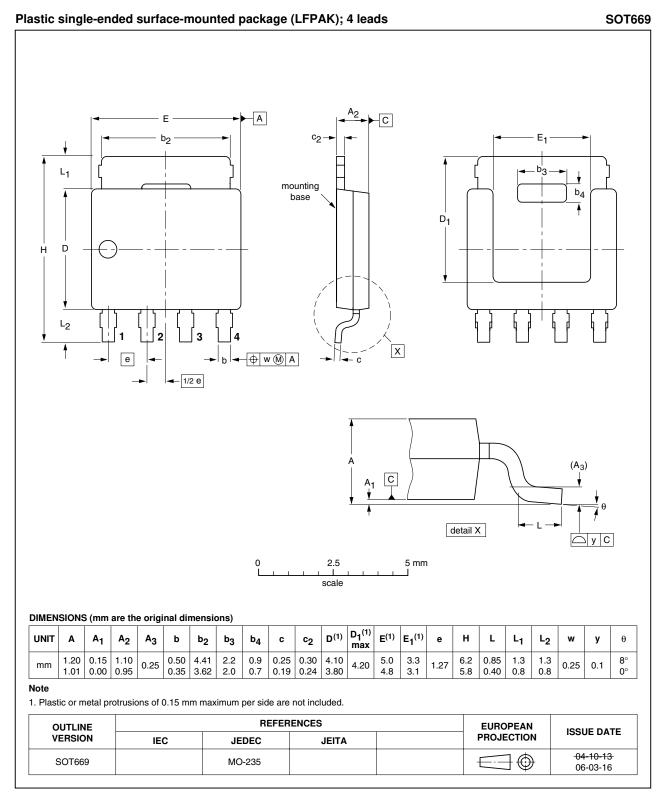


Fig 17. Package outline SOT669 (LFPAK)

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BUK7Y53-100B

N-channel TrenchMOS standard level FET

8. Revision history

Table 7. Revision I	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y53-100B v.3	20101013	Product data sheet	-	BUK7Y53-100B_2
Modifications:	 Status change 	ed from objective to product.		
BUK7Y53-100B_2	20100211	Objective data sheet	-	BUK7Y53-100B_1

N-channel TrenchMOS standard level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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N-channel TrenchMOS standard level FET

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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile1
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values
5	Thermal characteristics5
6	Characteristics6
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status12
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
10	Contact information13